# For Fuji Electric 6MBI75VA-060-50

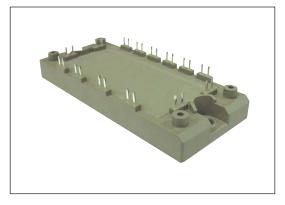
# IGBT MODULE (V series) 600V / 75A / 6 in one package

# Features

Compact Package P.C.Board Mount Low VCE (sat)

#### Applications

Inverter for Motor Drive AC and DC Servo Drive Amplifier Uninterruptible Power Supply Industrial machines, such as welding machines



## Maximum Ratings and Characteristics

## • Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items		Symbols	Conditions	Conditions		Units		
	Collector-Emitter voltage		Vces				V	
	Gate-Emitter voltage		V <sub>ges</sub>				V	
rter	Collector current		lc	Continuous	Tc=80°C	75		
a			Іср	1ms	Tc=80°C	150	^	
Ē			-lc		· · · ·		A	
			-lc pulse	1ms		150		
	Collector power dissipation		Pc	1 device		275	W	
Jur	Junction temperature		Tj			175		
Operating junciton temperature (under switching conditions)		Тјор			150	°C		
Case temperature		Тс			125			
Storage temperature		Tstg			-40 to +125			
lso	lation voltage	between terminal and copper base (*1) between thermistor and others (*2)	V <sub>iso</sub>	AC : 1min.	AC : 1min.		VAC	
Sci	rew torque	Mounting (*3)	-	M5	M5		N m	

Note \*1: All terminals should be connected together during the test.

Note \*2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note \*3: Recommendable value : 2.5-3.5 Nm (M5)

#### • Electrical characteristics (at Tj= 25°C unless otherwise specified)

	Cumpholo	Conditions		Characteristics			11
ems	Symbols			min.	typ.	max.	Units
Zero gate voltage collector current	Ices	V <sub>GE</sub> = 0V, V <sub>CE</sub> = 600V		-	-	1.0	mA
Gate-Emitter leakage current	Iges	$V_{GE} = 0V, V_{GE} = \pm 20V$		-	-	200	nA
Gate-Emitter threshold voltage	V <sub>GE (th)</sub>	V <sub>CE</sub> = 20V, Ic = 75mA		6.2	6.7	7.2	V
Collector-Emitter saturation voltage		V <sub>GE</sub> = 15V I <sub>c</sub> = 75A	Tj=25°C	-	2.00	2.45	- V
	V <sub>CE (sat)</sub> (terminal)		Tj=125°C	-	2.30	-	
	(terriniar)		Tj=150°C	-	2.50	-	
		V <sub>GE</sub> = 15V I <sub>c</sub> = 75A	Tj=25°C	-	1.60	2.05	
	V <sub>CE (sat)</sub> (chip)		Tj=125°C	-	1.90	-	
	(cmp)		Tj=150°C	-	2.10	-	
Internal gate resistance	Rg(int)	-		-	0	-	Ω
Input capacitance	Cies	V <sub>CE</sub> = 10V, V <sub>GE</sub> = 0V, f = 1MHz		-	4.9	-	nF
Turn-on time	ton		-	0.36	1.20	μs	
	tr	V <sub>cc</sub> = 300V I <sub>c</sub> = 75A -V <sub>GE</sub> = +15 / -15V		-	0.25		0.60
	tr (i)			-	0.07		-
Town off the s	toff	$R_{\rm g} = 30\Omega$	-	0.52	1.20		
Turn-off time	tf			-	0.03		0.45
Forward on voltage			Tj=25°C	-	2.00	2.45	- V
	V <sub>F</sub> (terminal)	I⊧ = 75A	Tj=125°C	-	1.90	-	
	(terminal)		Tj=150°C	-	1.85	-	
		I⊧ = 75A	Tj=25°C	-	1.60	2.05	
	V <sub>F</sub> (chip)		Tj=125°C	-	1.50	-	
	(Chip)		Tj=150°C	-	1.45	-	
Reverse recovery time	trr	I⊧ = 75A		-	-	0.35	μs
Projetanes		T = 25°C		-	5000	-	Ω
Resistance B value	R	T = 100°C		465	495	520	
<b>B</b> value B T = 25 / 50°C				3305	3375	3450	K

#### • Thermal resistance characteristics

Items	Symbols	Conditions	Characteristics			Units
Items		Conditions	min.	typ.	max.	Units
Thermal resistance (1device)	Rth(j-c)	Inverter IGBT	-	-	0.50	°C/W
mermanesistance (nevice)		Inverter FWD	-	-	0.95	
Contact thermal resistance (1device) (*4)	Rth(c-f)	with Thermal Compound	-	0.05	-	

Note \*4: This is the value which is defined mounting on the additional cooling fin with thermal compound.

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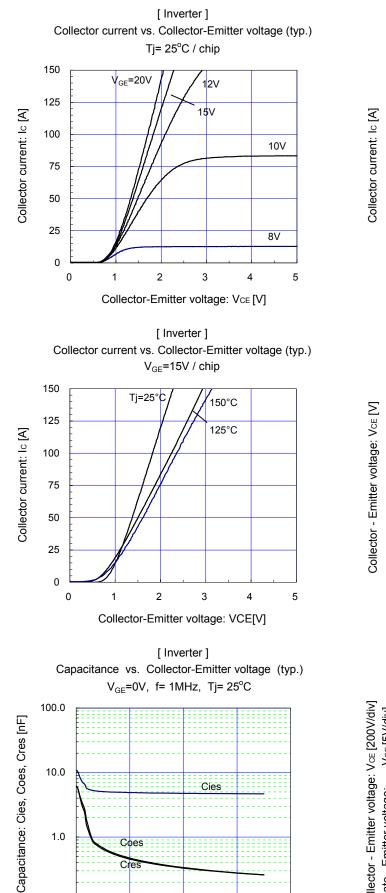
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[Inverter]

#### Characteristics (Representative)



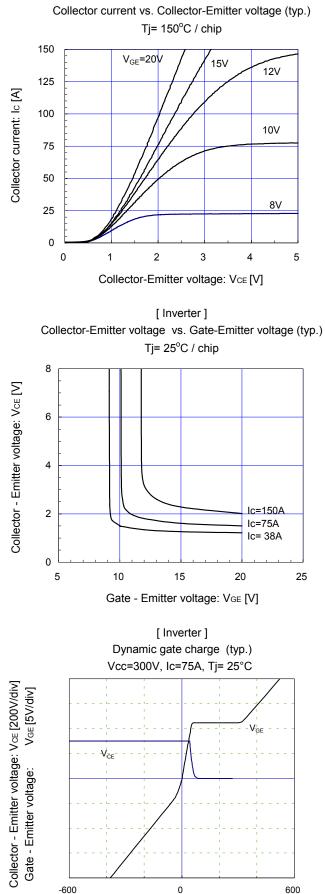
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Collector - Emitter voltage: VCE [V]

30

40

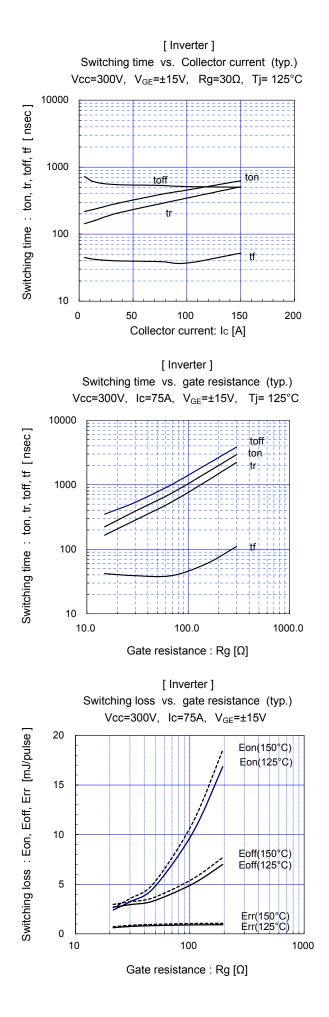
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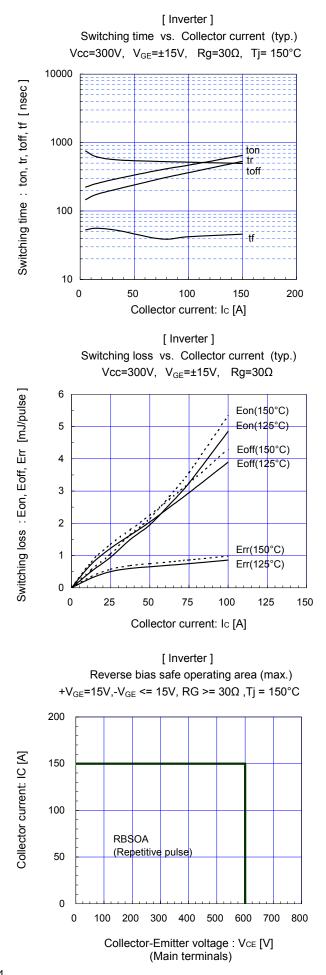


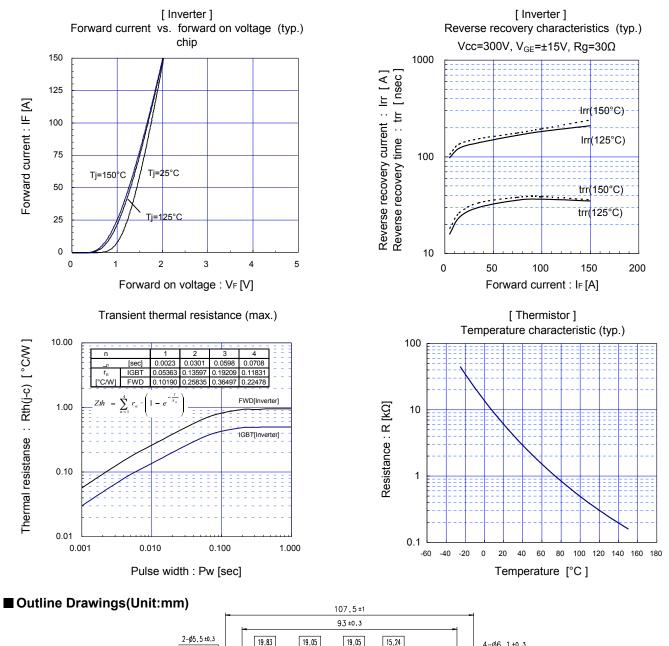
Gate charge: Qg [nC]

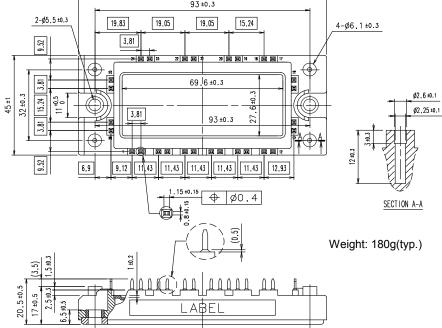
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#### Equivalent Circuit

